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Sharp Microelectronics PC4H510NIP

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PC4H510NIP

# PC4H510NIP

### Mini-flat Half-pitch Package, High Collector-emitter Voltage Photocoupler



#### Description

**PC4H510NIP** contains an IRED optically coupled to a phototransistor.

It is packaged in a 4-pin Mini-flat, half pitch type. Input-output isolation voltage(rms) is 2.5kV.

Collector-emitter voltage is 350V and CTR is 40% to 240% at input current of 5mA.

#### Features

- 1. 4-pin Mini-flat Half pitch package (Lead pitch : 1.27mm)
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. High collector-emitter voltage ( $V_{CEO}$  : 350V)
- 4. Isolation voltage between input and output (V $_{\text{iso}(\text{rms})}$  : 2.5kV)

#### Agency approvals/Compliance

- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. **PC4H51**)
- 2. Package resin : UL flammability grade (94V-0)

#### Applications

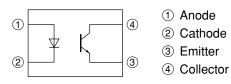
1. Modems

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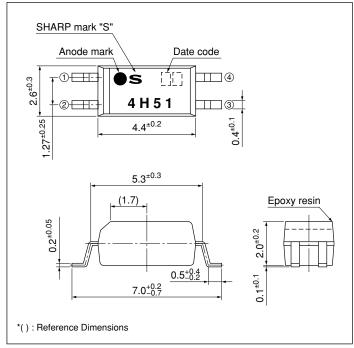
### PC4H510NIP

#### ■ Internal Connection Diagram



#### ■ Outline Dimensions

(Unit : mm)



Product mass : approx. 0.05g



PC4H510NIP

#### Date code (2 digit)

	1st o	digit		2nd digit			
	Year of p	roduction		Month of production			
A.D.	Mark	A.D	Mark	Month	Mark		
1990	А	2002	Р	January	1		
1991	В	2003	R	February	2		
1992	C	2004	S	March	3		
1993	D	2005	Т	April	4		
1994	Е	2006	U	May	5		
1995	F	2007	V	June	6		
1996	Н	2008	W	July	7		
1997	J	2009	X	August	8		
1998	K	2010	А	September	9		
1999	L	2011	В	October	0		
2000	М	2012	С	November	N		
2001	N	:	:	December	D		
2001		·	· ·	2 ccomoor			

repeats in a 20 year cycle

Country of origin Japan



<b>Absolute Maximum Ratings</b> $(T_a=25^{\circ}C)$							
	Parameter	Symbol	Rating	Unit			
	Forward current	I <sub>F</sub>	50	mA			
out	*1 Peak forward current	I <sub>FM</sub>	1	Α			
Input	Reverse voltage	V <sub>R</sub>	6	V			
	Power dissipation	Р	70	mW			
	Collector-emitter voltage	V <sub>CEO</sub>	350	V			
Output	Emitter-collector voltage	V <sub>ECO</sub>	6	V			
Out	Collector current	I <sub>C</sub>	50	mA			
-	Collector power dissipation	P <sub>C</sub>	150	mW			
-	Fotal power dissipation	P <sub>tot</sub>	170	mW			
(	Operating temperature	T <sub>opr</sub>	-25 to +100	°C			
Storage temperature		T <sub>stg</sub>	-55 to +125	°C			
*2]	solation voltage	V <sub>iso (rms)</sub>	2.5	kV			
*3 (	Soldering temperature	T <sub>sol</sub>	260	°C			

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⊧1	Pulse	width≤100µs,	Duty	ratio :	0.001

\*2 40 to 60%RH, AC for 1 minute, f=60Hz \*3 For 10s

#### ■ Electro-optical Characteristics

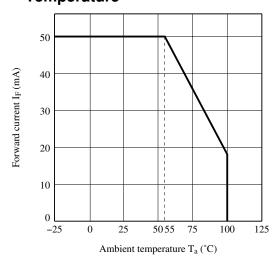
 $(T_a=25^{\circ}C)$ 

								( = )
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
	Forward voltage		$V_{\rm F}$	I <sub>F</sub> =20mA	-	1.2	1.4	V
Input	Reverse current		I <sub>R</sub>	V <sub>R</sub> =4V	-	-	10	μΑ
	Terminal capacitance		Ct	V=0, f=1kHz	_	30	250	pF
	Collector dark current		I <sub>CEO</sub>	$V_{CE}=200V, I_{F}=0$	-	-	1	μΑ
Output	Collector-emitter breakdown voltage		BV <sub>CEO</sub>	$I_{C}=0.1 \text{mA}, I_{F}=0$	350	-	-	V
	Emitter-collector breakdown voltage		BV <sub>ECO</sub>	$I_{E}=10\mu A, I_{F}=0$	6	_	_	V
	Current transfer ratio		I <sub>C</sub>	$I_F=5mA$ , $V_{CE}=5V$	2.0	4.0	12.0	mA
Transfer charac- teristics	Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	$I_F=20mA$ , $I_C=1mA$	-	0.1	0.3	V
	Isolation resistance		R <sub>ISO</sub>	DC500V, 40 to 60%RH	5×10 <sup>10</sup>	$1 \times 10^{11}$	-	Ω
	Floating capacitance		$C_{\mathrm{f}}$	V=0, f=1MHz	_	0.6	1.0	pF
	Cut-off frequency		$f_{C}$	$V_{CE}$ =5V, $I_C$ =2mA, $R_L$ =100 $\Omega$ -3dB	-	50	-	kHz
	Description	Rise time	t <sub>r</sub>	V 2V I 2m A B 1000	-	4	10	μs
	Response time	Fall time	t <sub>f</sub>	$V_{CE}=2V$ , $I_C=2mA$ , $R_L=100\Omega$	_	5	12	μs



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Fig.1 Forward Current vs. Ambient Temperature





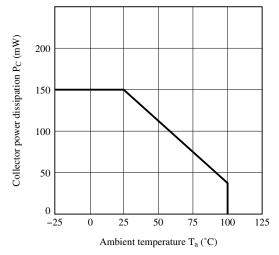


Fig.5 Peak Forward Current vs. Duty Ratio

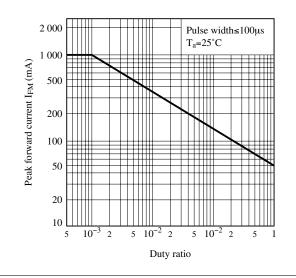
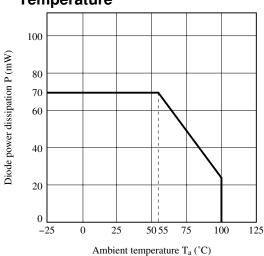


Fig.2 Diode Power Dissipation vs. Ambient Temperature



#### Fig.4 Total Power Dissipation vs. Ambient Temperature

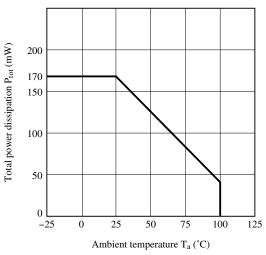
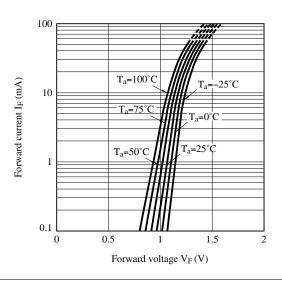


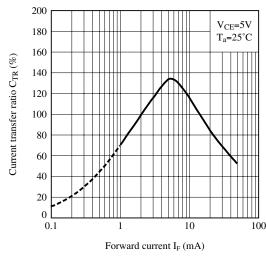
Fig.6 Forward Current vs. Forward Voltage



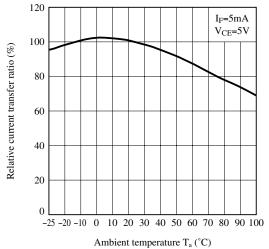
Sheet No.: D2-A02701EN



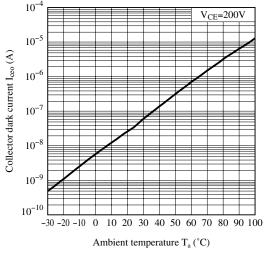
#### Fig.7 Current Transfer Ratio vs. Forward Current





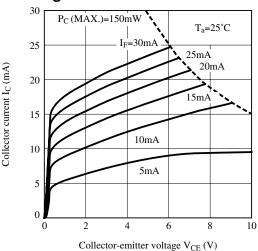






#### Fig.8 Collector Current vs. Collector-emitter Voltage

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# Fig.10 Collector - emitter Saturation Voltage vs. Ambient Temperature

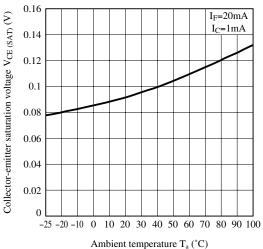
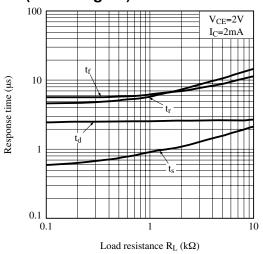


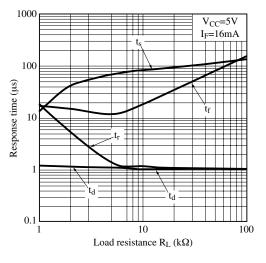
Fig.12 Response Time vs. Load Resistance (active region)



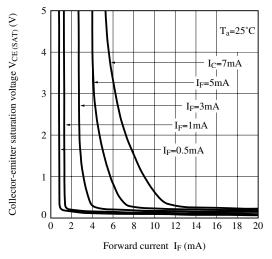
Sheet No.: D2-A02701EN



# Fig.13 Response Time vs. Load Resistance (saturation region)



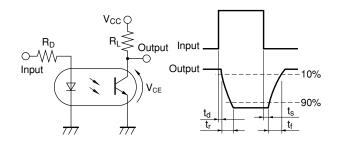
# Fig.15 Collector-emitter Saturation Voltage vs. Forward Current



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.

#### Fig.14 Test Circuit for Response Time

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Please refer to the conditions in Fig.12 and Fig.13



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#### Design Considerations

#### • Design guide

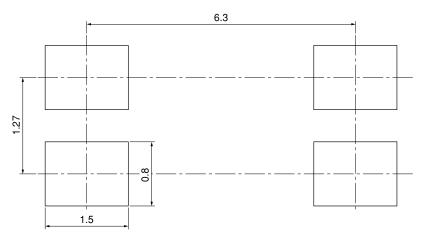
While operating at  $I_F < 1.0 \text{mA}$ , CTR variation may increase. Please make design considering this fact.

This product is not designed against irradiation and incorporates non-coherent IRED.

#### Degradation

In general, the emission of the IRED used in photocouplers will degrade over time. In the case of long term operation, please take the general IRED degradation (50% degradation over 5years) into the design consideration.

#### • Recommended Foot Print (reference)



(Unit : mm)

☆ For additional design assistance, please review our corresponding Optoelectronic Application Notes.



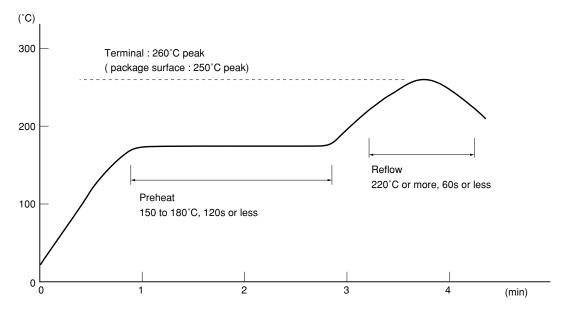
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#### Manufacturing Guidelines

#### Soldering Method

#### Reflow Soldering:

Reflow soldering should follow the temperature profile shown below. Soldering should not exceed the curve of temperature profile and time. Please don't solder more than twice.



#### Flow Soldering :

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 260°C and within 10s. Preheating is within the bounds of 100 to 150°C and 30 to 80s. Please don't solder more than twice.

#### Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C. Please don't solder more than twice.

#### Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



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#### • Cleaning instructions

#### Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3minutes or less

#### Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

#### Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

#### Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this device.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform) Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.



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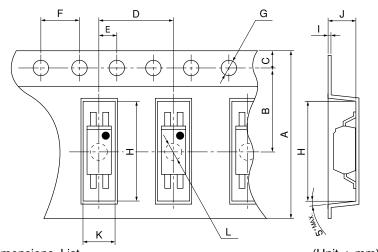
#### ■ Package specification

### • Tape and Reel package

Package materials

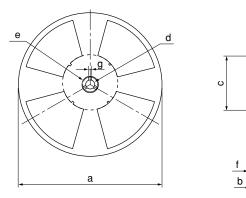
Carrier tape : A-PET (with anti-static material) Cover tape : PET (three layer system) Reel : PS

Carrier tape structure and Dimensions



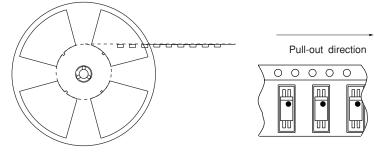
Dimensions List (Unit : mm)						
А	В	C	D	Е	F	G
$12.0^{\pm 0.3}$	$5.5^{\pm 0.1}$	$1.75^{\pm 0.1}$	$8.0^{\pm 0.1}$	$2.0^{\pm 0.1}$	$4.0^{\pm 0.1}$	$\phi 1.5^{+0.1}_{-0}$
Н	Ι	J	K	L		
$7.5^{\pm 0.1}$	$0.3^{\pm 0.05}$	2.3 <sup>±0.1</sup>	3.1 <sup>±0.1</sup>	$\phi 1.6^{+0.1}_{-0}$		

#### Reel structure and Dimensions



Dimensio	ns List	(Unit : mm)		
а	b	с	d	
330	13.5 <sup>±1.5</sup>	$100^{\pm 1.0}$	13 <sup>±0.5</sup>	
e	f	g		
23±1.0	2.0 <sup>±0.5</sup>	2.0 <sup>±0.5</sup>		

#### Direction of product insertion



[Packing : 3 000pcs/reel]



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- --- Office automation equipment
- --- Telecommunication equipment [terminal]
- --- Test and measurement equipment
- --- Industrial control
- --- Audio visual equipment
- --- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

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- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.

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